

MJE3439

NPN Silicon High-Voltage Power Transistor

This device is designed for use in line-operated equipment requiring high f_T .

Features

- High DC Current Gain – $h_{FE} = 40-160 @ I_C = 20 \text{ mAdc}$
- Current Gain Bandwidth Product – $f_T = 15 \text{ MHz (Min) @ } I_C = 10 \text{ mAdc}$
- Low Output Capacitance – $C_{ob} = 10 \text{ pF (Max) @ } f = 1.0 \text{ MHz}$
- Pb-Free Package is Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	350	Vdc
Collector-Base Voltage	V_{CB}	450	Vdc
Emitter-Base Voltage	V_{EB}	5.0	Vdc
Collector Current – Continuous	I_C	0.3	Adc
Base Current	I_B	150	mAdc
Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	15 0.12	W mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Case	θ_{JC}	8.33	$^\circ\text{C/W}$

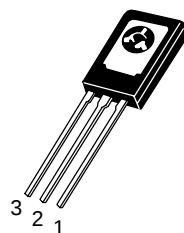
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.



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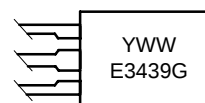
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**0.3 AMPERE
POWER TRANSISTOR
NPN SILICON
350 VOLTS, 15 WATTS**



TO-225
CASE 77
STYLE 1

MARKING DIAGRAM



Y = Year
WW = Work Week
E3439 = Device Code
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping
MJE3439	TO-225	500 Units/Box
MJE3439G	TO-225 (Pb-Free)	500 Units/Box

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MJE3439

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ($I_C = 5.0\text{ mAdc}$, $I_B = 0$)	$V_{CEO(sus)}$	350	–	Vdc
Collector Cutoff Current ($V_{CE} = 300\text{ Vdc}$, $I_B = 0$)	I_{CEO}	–	20	μAdc
Collector Cutoff Current ($V_{CE} = 450\text{ Vdc}$, $V_{EB(off)} = 1.5\text{ Vdc}$)	I_{CEX}	–	500	μAdc
Collector Cutoff Current ($V_{CB} = 350\text{ Vdc}$, $I_E = 0$)	I_{CBO}	–	20	μAdc
Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	–	20	μAdc
ON CHARACTERISTICS				
DC Current Gain ($I_C = 2.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$) ($I_C = 20\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	h_{FE}	30 15	– 200	–
Collector–Emitter Saturation Voltage ($I_C = 50\text{ mAdc}$, $I_B = 4.0\text{ mAdc}$)	$V_{CE(sat)}$	–	0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = 50\text{ mAdc}$, $I_B = 4.0\text{ mAdc}$)	$V_{BE(sat)}$	–	1.3	Vdc
Base–Emitter On Voltage ($I_C = 50\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$)	$V_{BE(on)}$	–	0.8	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product ($I_C = 10\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 5.0\text{ MHz}$)	f_T	15	–	MHz
Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	–	10	pF
Small–Signal Current Gain ($I_C = 5.0\text{ mAdc}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$)	h_{fe}	25	–	–

MJE3439

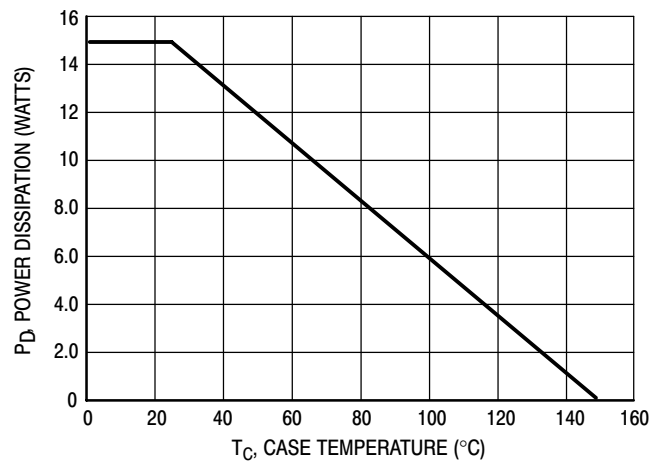


Figure 1. Power-Temperature Derating Curve

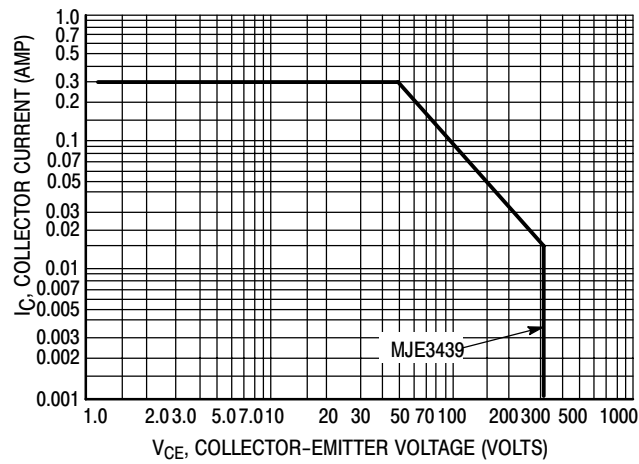


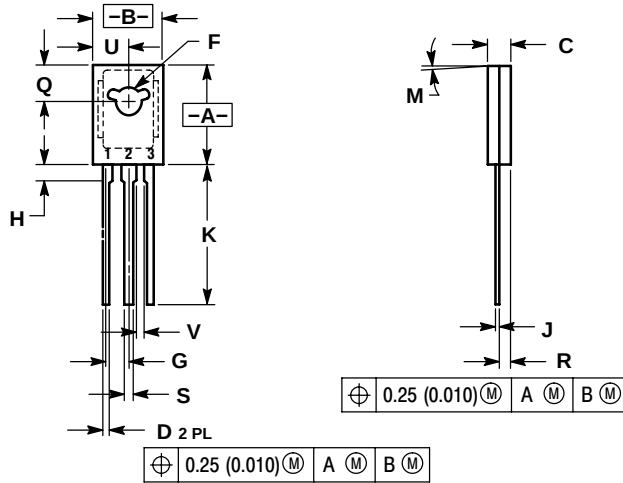
Figure 2. Active-Region Safe Operating Area

The Safe Operating Area Curves indicate $I_C - V_{CE}$ limits below which the device will not enter secondary breakdown. Collector load lines for specific circuits must fall within the applicable Safe Area to avoid causing a catastrophic failure. To insure operation below the maximum T_J , power-temperature derating must be observed for both steady state and pulse power conditions.

MJE3439

PACKAGE DIMENSIONS

TO-225
CASE 77-09
ISSUE Z



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 077-01 THRU -08 OBSOLETE, NEW STANDARD 077-09.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.425	0.435	10.80	11.04
B	0.295	0.305	7.50	7.74
C	0.095	0.105	2.42	2.66
D	0.020	0.026	0.51	0.66
F	0.115	0.130	2.93	3.30
G	0.094 BSC		2.39 BSC	
H	0.050	0.095	1.27	2.41
J	0.015	0.025	0.39	0.63
K	0.575	0.655	14.61	16.63
M	5° TYP		5° TYP	
Q	0.148	0.158	3.76	4.01
R	0.045	0.065	1.15	1.65
S	0.025	0.035	0.64	0.88
U	0.145	0.155	3.69	3.93
V	0.040	---	1.02	---

STYLE 1:

1. EMITTER
2. COLLECTOR
3. BASE

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